Toshiba BiCD Integrated Circuit Silicon Monolithic

TB7100F

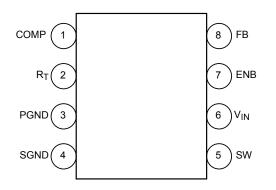
Step-down DC-DC Converter IC

The TB7100F is a single-chip step-down DC-DC converter IC. Equipped with a built-in high-speed and low on-resistance power MOSFET, and utilizing a chopper circuit, this IC can achieve a high efficiency in a wide load current range.

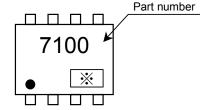
Features

- Capable of high current drive (I_{OUT} = maximum of 700 mA), using only a few external components
- High efficiency (η = 90% or higher) (@V_{IN} = 5V, V_{OUT} = 3.3V, and I_{OUT} = 300 mA).
- Operating voltage (VIN) range: 3 to 5.5 V
- Low on-resistance (R_{DS(ON)}): 0.27 Ω (typ.) if V_{IN} = 5 V
- High oscillation frequency of 550 kHz (typ.), making it possible to use small external components.
- Uses external phase compensation, assuring a high degree of design freedom in selecting external components and determining a loop response.
- Employs a current mode architecture with excellent fast load response.
- A small surface mount-type ceramic capacitor can be used as an output smoothing capacitor.
- Housed in a small surface-mount package (PS-8) with a low thermal resistance.

Pin Assignment



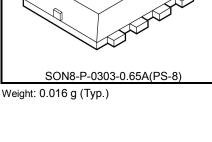
Marking



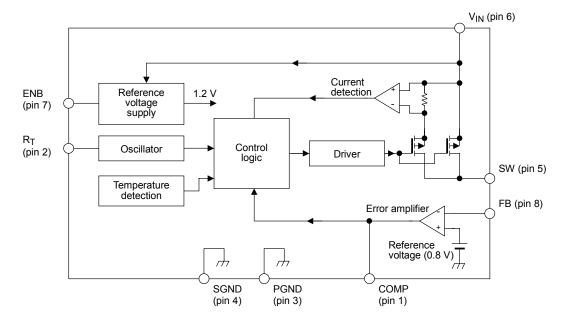
• The dot (•) on the top surface indicates pin 1.

*: Lot number

Due to its MOS structure, this product is sensitive to electrostatic discharge. Handle with care.



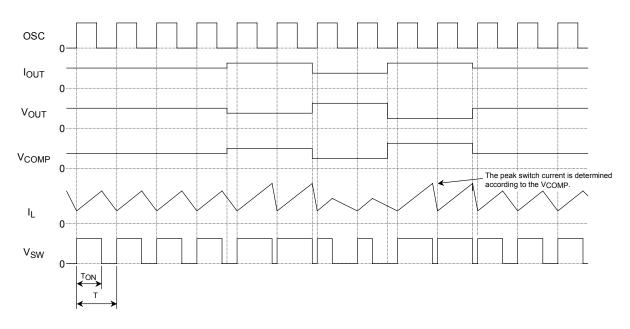
Block Diagram



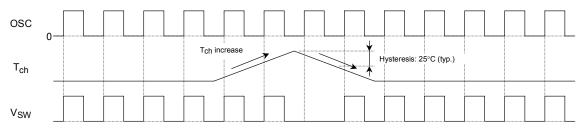
Pin Descriptions

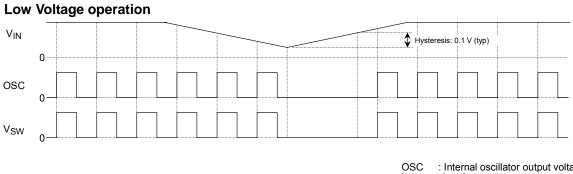
Pin No.	Pin Symbol	Pin Description			
1	COMP	Pin for connecting an error amplifier phase compensation resistor and capacitor.			
2	R _T	Oscillation frequency setting pin for connecting a resistor to the internal oscillation circuit. Connecting 120 k Ω to this pin operates the oscillation circuit at 550 kHz (typ.).			
3	PGND	Power ground			
4	SGND	Signal ground			
5	SW	Switching pin. A P-channel MOSFET is connected between the V _{IN} and SW pins. The peak switch current corresponding to the voltage that is generated at the COMP pin flows through the power MOSFET. The rating of this peak switch current is 1.0 A (min).			
6	V _{IN}	Input pin. This pin is placed in the standby state if V_{ENB} = low. 1 $_\mu\!A$ or lower operating current			
7 ENB Enable pin. This pin is connected to the CMOS inverter. Applying 3 to this pin starts the internal circuit to perform switching control.		Enable pin. This pin is connected to the CMOS inverter. Applying 3.5 V or higher (@ V_{IN} = 5 V) to this pin starts the internal circuit to perform switching control.			
8	FB	Output voltage feedback pin. This is connected to the internal error amplifier, which is supplied with a reference voltage of 0.8 V (typ.).			

Timing Chart



Overheat state operation





OSC I _{OUT}	: Internal oscillator output voltage : Load current
VOUT	: Output voltage
VCOME	COMP pin voltage
li	: Inductor current
V _{SW}	: SW pin voltage
VIN	: Input pin voltage
T _{ch}	: Channel temperature

Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit
Input voltage	V _{IN}	-0.3~6	V
Switch pin voltage	V _{SW}	-0.3~6	V
Feedback pin voltage	V _{FB}	-0.3~6	V
Enable pin voltage	V _{ENB}	-0.3~6	V
Input-enable pin voltage	V _{ENB} -V _{IN}	V _{ENB} -V _{IN} <0.3	V
Power dissipation (Note 1)	PD	0.7	W
Operating temperature	Topr	-40~85	°C
Channel temperature	T _{ch}	150	°C
Storage temperature	T _{stg}	-55~150	°C

Thermal Resistance Characteristic

Characteristics	Symbol	Max	Unit
Thermal resistance, channel and ambient	R _{th (ch-a)}	178.6 (Note 1)	°C /W

(Note 1)

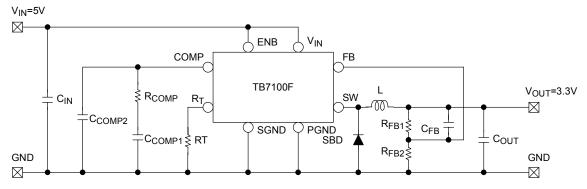
Glass epoxy board

Material : FR-4 25.4 × 25.4 × 0.8 (Unit: mm)

Electrical Characteristics (unless otherwise specified: Ta = 25°C and V_{IN} = 3 to 5.5 V)

Characteristics		Symbol	Test circuit	Test condition	Min	Тур.	Max	Unit
Operating supply voltage		V _{IN(OPR)}	-	-	3	5	5.5	V
Load current		I _{OUT}	-	-	_	_	700	mA
Operating curre	ent	I _{IN}	_	V_{IN} = 5 V, V_{ENB} = 5 V, V_{FB} = 0.7 V R _T = 120 kΩ	-	570	750	μA
Standby curren	ıt	I _{IN(STBY)}	_	V_{IN} = 5 V, V_{ENB} = 0 V, V_{FB} = 0.9 V	Ι	_	1	μA
Enable pin threshold voltage		VIH	_	V _{IN} = 5 V	3.5	_	—	V
	Shou voltage	VIL	_	V _{IN} = 5 V		—	1.5	V
Enable pin inpu	ut current	IIH		V _{IN} = 5 V, V _{ENB} = 5 V		—	20	μA
Feedback pin current		I _{FB}	-	-	-1	-	1	μA
Feedback pin voltage		V _{FB}	_	-	0.776	0.8	0.824	V
Feedback pin line regulation		$\Delta V_{\text{FB}(\text{LINE})}$	_	V _{IN} = V _{ENB} = 3 V~5 V	-	1.6	5	mV/V
High-side on-state resistance		R _{DS(ON)}	_	V _{IN} = 5 V, V _{ENB} = 5 V, I _{SW} = - 0.5 A	_	0.27	0.6	Ω
High-side leakage current		I _{LEAK}	-	V _{IN} = 5 V, V _{ENB} = 0 V, V _{SW} = 0 V	-	-	-1	μA
Oscillation frequency		fosc	_	V _{IN} = 5 V, V _{ENB} = 5 V, R _T = 120 k Ω	_	550	_	kHz
Error amplifier conductance		9m	_	$V_{IN} = 5 V$, $V_{ENB} = 5 V$ $I_{COMP} = \pm 20 \mu A$	_	800	_	μS
Peak switch current		I _{SW(PEAK)}	_	—	1.0	1.5	—	А
Undervoltage protection	Detection	V _{UV}	_	-	2.3	2.5	2.7	V
	Hysteresis	ΔV_{UV}	_	-	—	0.1	-	V
Overheat	Detection	T _{SD}	_	-	125	145	_	°C
protection	Hysteresis	ΔT_{SD}		-	-	25	_	°C

Application Circuit Example





Component constants

The following values are given only for your reference and may need tuning depending on your input/output conditions and board layout.

 C_{IN} : Input smoothing capacitance of 10 μ F (multilayer ceramic capacitor JMK212BJ106KG, manufactured by Taiyo Yuden Co.,

Ltd.)

 C_{OUT} : Output smoothing capacitance of 10 μ F

(multilayer ceramic capacitor JMK212BJ106KG manufactured by Taiyo Yuden Co., Ltd.)

C_{COMP1}: Error amplifier phase compensation capacitance of 3300 pF (@ V_{IN} = 5 V, V_{OUT} = 3.3 V, and R_T = 120 kΩ)

 C_{COMP2} : Error amplifier phase compensation capacitance (not used if phase compensation is possible only with R_{COMP} and C_{COMP1})

C_{FB}: Error amplifier phase compensation capacitance (not used if phase compensation is possible only with R_{COMP} and C_{COMP1})

R_{COMP}: Error amplifier phase compensation resistance of 1 k Ω (@ V_{IN} = 5 V, V_{OUT} = 3.3 V, and R_T = 120 k Ω)

RT: Oscillation frequency setting resistance of 120 k Ω (@ f_{OSC} = 550 kHz)

R_{FB1}: Output voltage setting resistance of 75 k Ω (@ V_{IN} = 5 V, V_{OUT} = 3.3 V, and R_T = 120 k Ω)

R_{FB2}: Output voltage setting resistance of 24 k Ω (@ V_{IN} = 5 V, V_{OUT} = 3.3 V, and R_T = 120 k Ω)

L: Inductor 6.8 μ H (@ V_{IN} = 5 V, V_{OUT} = 3.3 V, and R_T = 120 k_Ω); CDRH4D28C/LD series, manufactured by Sumida Corporation SBD: Schottky barrier diode CRS06 (@ V_{RRM} = 20 V and I_{F(AV)} = 1 A), manufactured by Toshiba Corporation

How to use

Setting the Inductance

The required inductance can be calculated by using the following equation:

$$L = \frac{V_{OUT}}{f_{OSC} \cdot \Delta I_L} \cdot \left(1 - \frac{V_{OUT}}{V_{IN}}\right) \quad \cdots \quad (1)$$

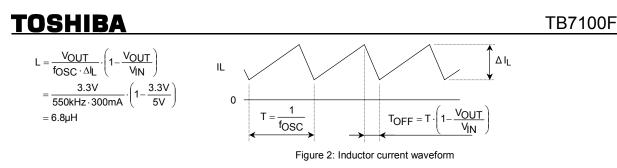
$$V_{IN}: \text{ Input voltage (V)}$$

$$V_{OUT}: \text{ Output voltage (V)}$$

 f_{OSC} : Oscillation frequency (Hz) ΔI_L : Inductor ripple current (A)

* Generally, Δ_{IL} should be set to 30% to 40% of the peak current flowing through the inductor. For the TB7100F, set ΔI_L to 0.3 A, as its peak switch current [$I_{SW(PEAK)}$] is 1 A (min). Therefore select an inductor whose current rating is no lower than the peak switch current [1 A (min)] of the TB7100F. If the current rating is exceeded, the inductor becomes saturated, leading to an unstable DC-DC converter operation.

If V_{IN} = 5 V and V_{OUT} = 3.3 V, the required inductance can be calculated as below. Be sure to select an inductor with an optimum constant by taking V_{IN} variations into consideration.



Setting the output voltage

For the TB7100F, the output voltage is set using the voltage dividing resistors R_{FB1} and R_{FB2} according to the reference voltage [0.8 V (typ.)] of the error amplifier connected to the FB pin. If the R_{FB1} value is extremely large, a delay can occur due to a parasitic capacitance at the FB pin. Keep the R_{FB1} value within approximately 100 k Ω . The output voltage can be calculated by using equation 2 below. It is recommended that a resistor with a precision of $\pm 1\%$ or higher be used for setting the output voltage.

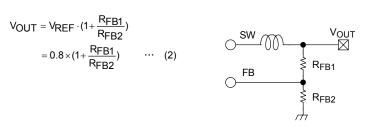


Figure 3: Output voltage setting resistors

Setting the COMP pin for phase compensation

The COMP pin is intended to compensate for any phase delay that may occur inside or outside the TB7100F. Phase compensation is carried out using resistors and capacitors connected to the COMP pin. The constants of the phase compensation components are selected by first specifying R_{COMP} and C_{COMP} to be, respectively, 1 k Ω and 3300 pF. However, it is necessary to measure the SW pin oscillation waveform and load response characteristics and tune the component constants, optimizing them so as to optimize the influence of your board layout and component characteristics. When tuning component constants, carefully evaluate them while taking component variations and temperature characteristics into consideration.

Table 1 lists the relationships between the R_{COMP} and C_{COMP} constants. Use these as a guideline in selecting constants.

		SW pin waveform stability	Load response characteristic
Dear	Large	Decreased	Increased
R _{COMP}	Small	Increased	Decreased
0	Large	Increased	Decreased
CCOMP	Small	Decreased	Increased

Table 1: Relationships between R_{COMP} and C_{COMP} values

Output capacitor

The capacitance of the output ceramic capacitor is greatly affected by temperature. Select a product whose temperature characteristics (such as B-characteristic) are excellent. Set the capacitance to an optimum value that meets the set's ripple requirement and is not lower than 10 μ F. It is more difficult to achieve phase compensation with ceramic capacitors than with tantalum electrolytic capacitors because the equivalent series resistance (ESR) of the former is much lower than that of the latter. For this reason, perform a careful evaluation when using ceramic capacitors.

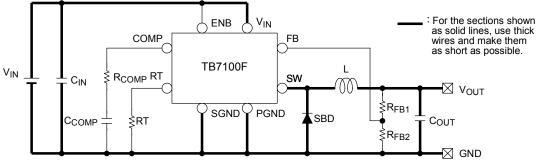
Miscellaneous

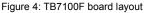
Generally, a DC-DC converter under current mode control may fail to operate at a constant duty ratio if the duty ratio is 50% or higher. This IC incorporates slope compensation to achieve as stable an operation as possible.

However, a delay in the internal circuit may prevent the IC from operating at a constant duty ratio when the duty ratio is 50% or so depending on your input/output and load conditions.

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Board layout



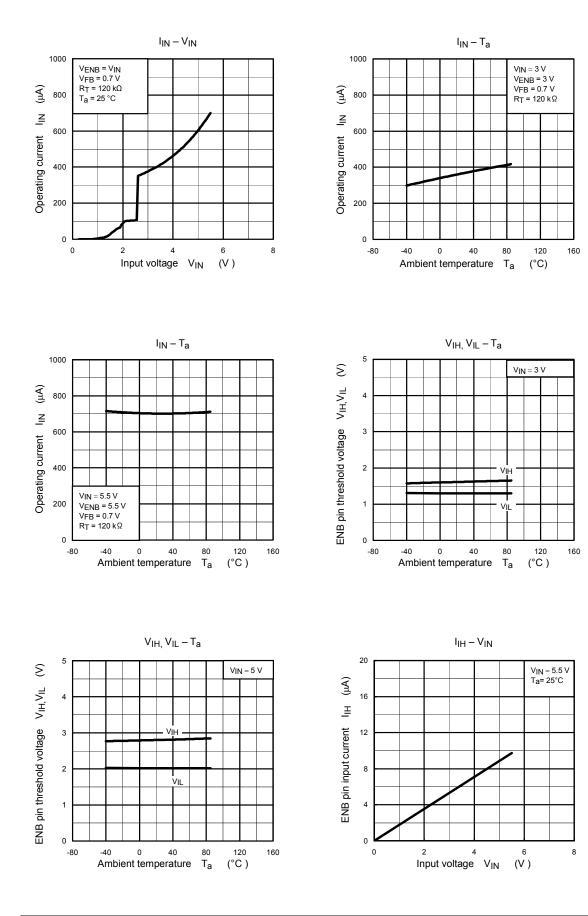


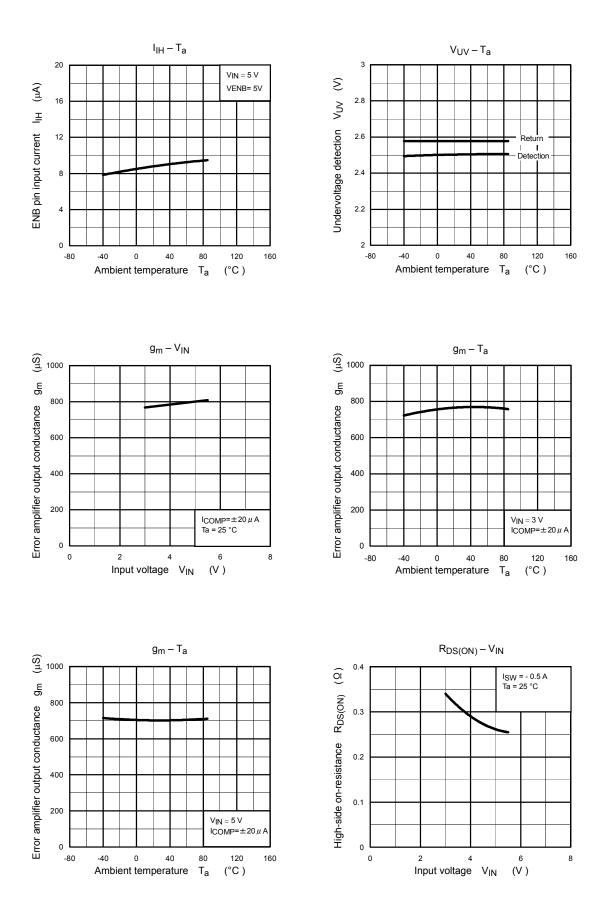
- For the supply voltage, output, and ground lines, which carry high current, use thick wires and make them as short as possible so as to keep their impedance low.
- Place the input/output smoothing capacitors and inductor as close to the IC as possible.
- For the output voltage monitoring FB line, keep the wire as short as possible to counter the effects of noise.
- Design the layout to ensure that no voltage potential difference occurs between the SGND and PGND pins. Otherwise, the operation of the IC may become unstable.
- It is recommended you place the components connected to the COMP and R_T pins as close to the IC as possible and ground them at a single point so as stabilize the voltage at these pins. Otherwise, the operation of the IC may become unstable.
- The leakage current of the SBD may increase at high temperatures, leading to a thermal runaway. Ensure, therefore, that no problem with the SBD will occur even under the worst-case conditions.

A DC-DC converter using this IC is greatly affected by the characteristics of external components and the impedance of the PCB. Make sure that there is no problem with the dependency of the load current on its output voltage and load response even when any component constant deviates from the corresponding value given above for reference purposes. Also, design the DC-DC converter by selecting optimum external components and a suitable board layout so that no rating of this IC will be exceeded.

Precautions

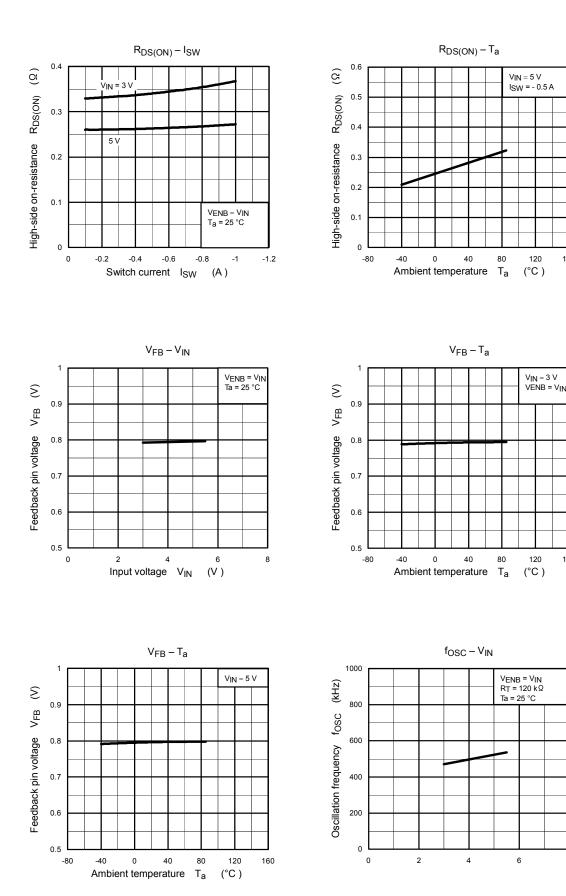
- If the voltage between the input and output is low, the influence of the on-state voltage of the switch power MOSFET is greater, causing the voltage across the inductor to decrease. For this reason, it may become impossible for the required inductor current to flow, resulting in lower performance or unstable operation of the DC-DC converter. As a rough standard, keep the input-output voltage potential difference at or above 1 V, taking the on-state voltage of the power MOSFET into consideration.
- The lowest output voltage that can be set is 0.8 V (typ.).
- There is an antistatic diode between the ENB and V_{IN} pins. The voltage between the ENB and V_{IN} pins should satisfy the rating V_{ENB} V_{IN} < 0.3 V



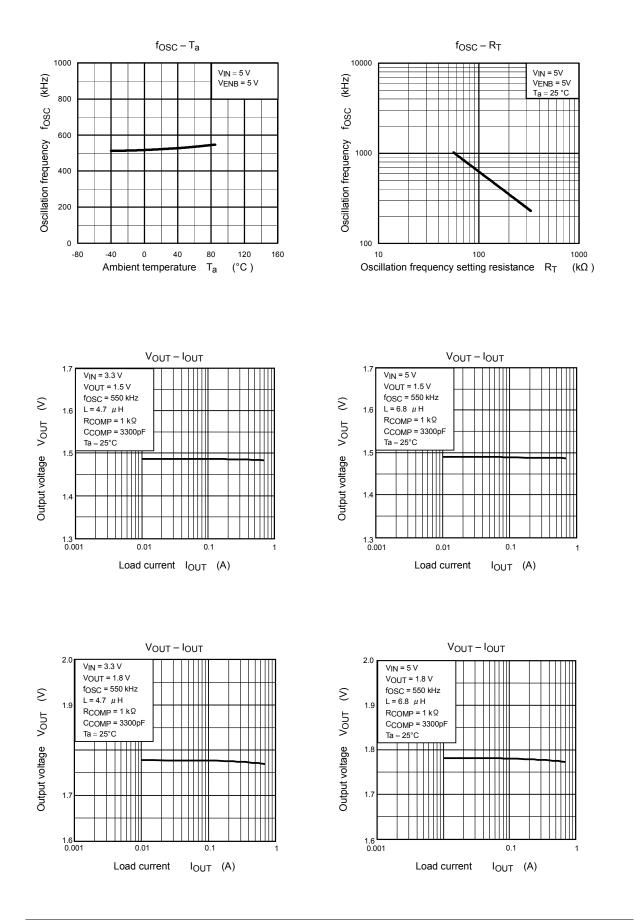


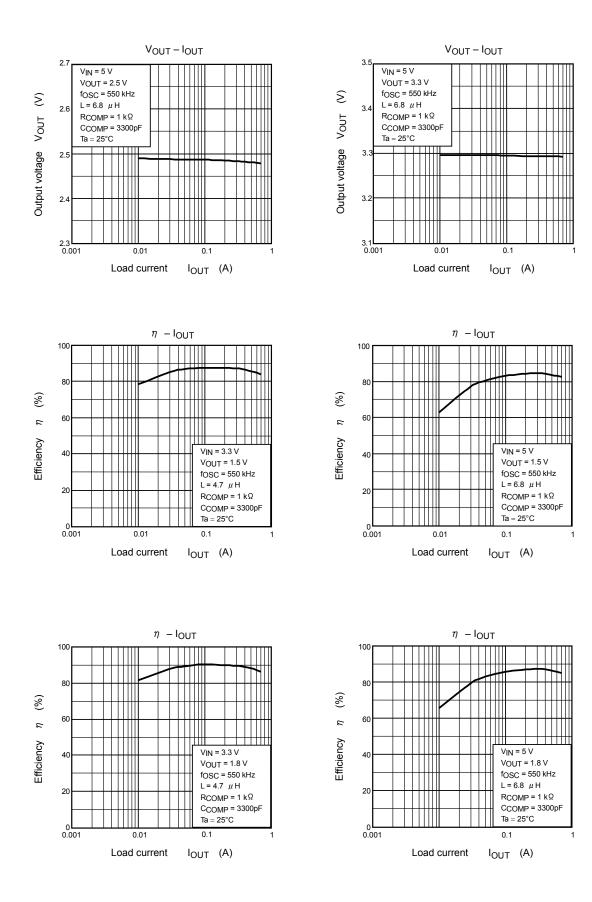
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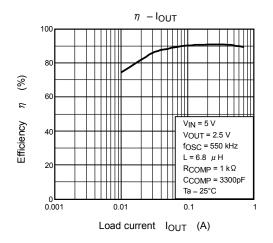
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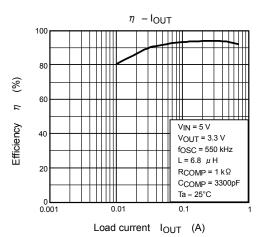


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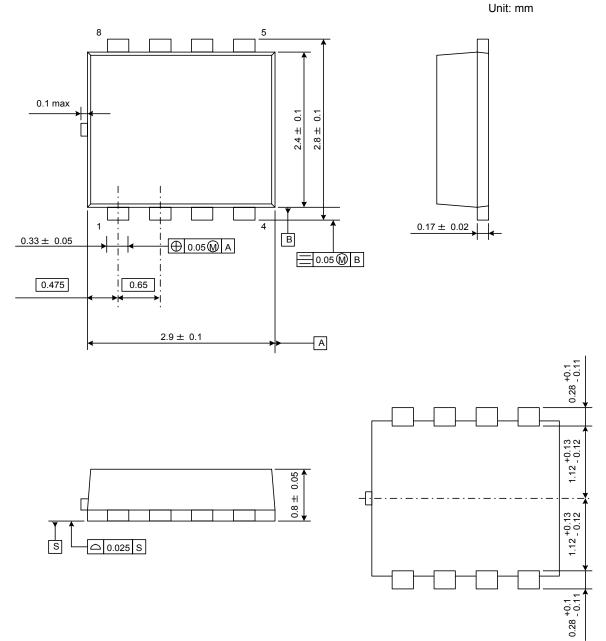




P_D – T_a 1 25.4 × 25.4 × 0.8mm Refer to Note 1 for the pattern when mounted on a glass epoxy board. Ś 0.8 Power dissipation PD 0.6 0.4 • 0.2 • 0 40 0 80 120 160 Ambient temperature T_a (°C)

Package dimensions

SON8-P-0303-0.65A



Weight: 0.016 g (Typ.)

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